

Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	To Be Assigned 10/760966
				Filing Date	Concurrently Herewith 1-20-04
				First Named Inventor	Zhibo Zhang
				Group Art Unit	2813
				Examiner Name	HOGANS
Sheet 1 of 2	Attorney Docket Number 5051-563DV				

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code (if known)			
DJA	1.	6,359,288	B1	Ying et al.	03-19-2002	
	2.	6,231,744	B1	Ying et al.	05-15-2001	
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	7.	5,306,661		Tonucci et al.	04-1994	
	8.	6,177,291		Eriguchi et al.	01-2001	

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		Office	Number	Kind Code (if known)				
DJA	9.	EP	0 178 831	B1	Alcan International Limited	08-07-1991		


OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
DJA	10.	Auth, Christopher P., "Scaling Theory for Cylindrical, Fully-Depleted, Surrounding-Gate MOSFET's," IEEE Electron Device Letters, Vol. 18, No. 2, February 1997, pp. 74-76	
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DJA	12.	Hisamoto et al., "A Folded-channel MOSFET for Deep-sub-tenth Micron Era," Department of Electrical Engineering and Computer Sciences, University of California at Berkeley, 1998 IEEE, 3 pages	
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DJA	15.	Masuda et al., "Highly ordered nanochannel-array architecture in anodic alumina," Appl. Phys. Lett. 71, No. 19, November 10, 1997, pp. 2770-2772	
DJA	16.	Risch et al., "Vertical MOS Transistors with 70nm Channel Length," IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498	
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Examiner Signature 	Date Considered 1-18-05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet 2 of 2	Attorney Docket Number	5051-563DV	

DA	23.	Faist et al., "Mid-infrared field-tunable intersubband electroluminescence at room temperature by photon-assisted tunneling in coupled-quantum wells," Appl. Phys. Lett., Vol. 64, No. 9, February 28, 1994, pp. 1144-1146
DA	24.	Guha et al., "Selective area metalorganic molecular-beam epitaxy of GaN and the growth of luminescent microcolumns on Si/SiO ₂ ," Applied Physics Letters, Vol. 75, No. 4, July 26, 1999, pp. 463-465
DA	25.	Hergenrother et al., "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length," 1999 IEEE, pp. IEDM 99-75 through 99-78
DA	26.	Hinzer et al., "Widely tunable self-assembled quantum dot lasers," J. Vac. Sci. Technol. A, Vol. 18, No. 2, Mar/Apr 2000, pp. 578-581
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DA	32.	Misra et al., "Electric Properties of Composite Gate Oxides Formed by Rapid Thermal Processing," IEEE Transactions on Electron Devices, Vol. 43, No. 4, April 1996, pp. 636-646
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DA	36.	Pan et al., "Normal-incidence intersubband (In, Ga)As/GaAs quantum dot infrared photodetectors," Applied Physics Letters, Vol. 73, No. 14, October 5, 1998, pp. 1937-1939
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